# Low-power configurable multiple function gate Rev. 8 — 22 April 2014 P

Product data sheet

#### **General description** 1.

The 74LVC1G58 provides configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XOR, inverter and buffer. All inputs can be connected to  $V_{CC}$  or GND.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

All inputs (A, B and C) are Schmitt trigger inputs. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

#### 2. **Features and benefits**

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 V to 2.7 V)
  - JESD8B/JESD36 (2.7 V to 3.6 V).
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V.
- ±24 mA output drive (V<sub>CC</sub> = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C.



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### 3. Ordering information

#### Table 1.Ordering information

Type number	Package							
	Temperature range Name		Description	Version				
74LVC1G58GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363				
74LVC1G58GV	–40 °C to +125 °C	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457				
74LVC1G58GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886				
74LVC1G58GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891				
74LVC1G58GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115				
74LVC1G58GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202				

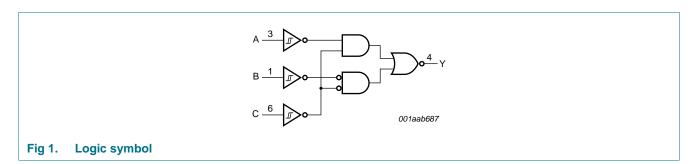
### 4. Marking

#### Table 2.Marking

Type number	Marking code <sup>[1]</sup>
74LVC1G58GW	YK
74LVC1G58GV	V58
74LVC1G58GM	YK
74LVC1G58GF	YK
74LVC1G58GN	YK
74LVC1G58GS	YK

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

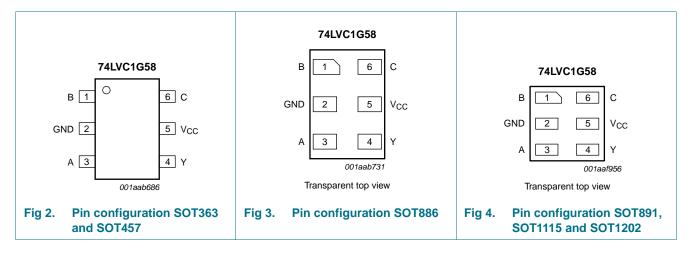
### 5. Functional diagram



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### 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3.   Pin description		
Symbol	Pin	Description
В	1	data input
GND	2	ground (0 V)
A	3	data input
Y	4	data output
V <sub>cc</sub>	5	supply voltage
С	6	data input

### 7. Functional description

#### Table 4.Function table

Inputs	Inputs				
C	В	Α	Y		
L	L	L	L		
L	L	Н	Н		
L	Н	L	L		
L	Н	Н	Н		
Н	L	L	Н		
Н	L	Н	Н		
Н	Н	L	L		
Н	Н	Н	L		

[1] H = HIGH voltage level; L = LOW voltage level

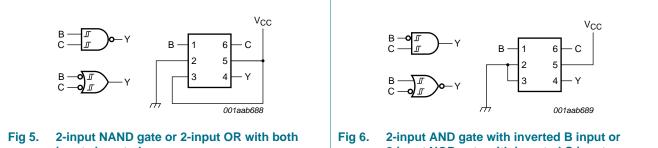
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### 7.1 Logic configurations

#### Table 5. **Function selection table**

Logic function	Figure
2-input NAND	see <u>Figure 5</u>
2-input NAND with both inputs inverted	see <u>Figure 8</u>
2-input AND with inverted input	see <u>Figure 6</u> and <u>7</u>
2-input NOR with inverted input	see <u>Figure 6</u> and <u>7</u>
2-input OR	see <u>Figure 8</u>
2-input OR with both inputs inverted	see <u>Figure 5</u>
2-input XOR	see <u>Figure 9</u>
Buffer	see <u>Figure 10</u>
Inverter	see <u>Figure 11</u>



inputs inverted

2-input NOR gate with inverted C input

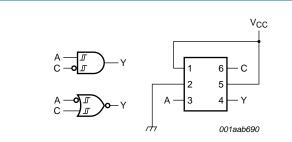


Fig 7. 2-input AND gate with inverted C input or 2-input NOR gate with inverted A input

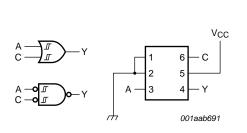
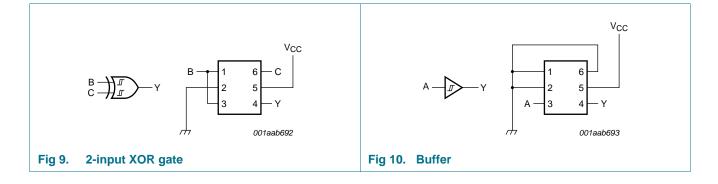
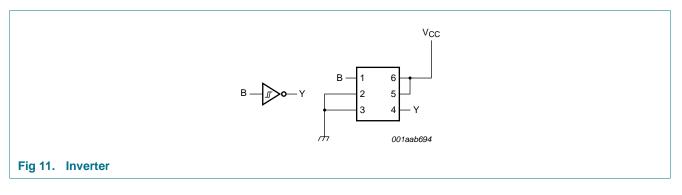


Fig 8. 2-input OR gate or 2-input NAND gate with both inputs inverted



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#### **Limiting values** 8.

#### Table 6. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+6.5	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V		-50	-	mA
VI	input voltage		[1]	-0.5	+6.5	V
Ι <sub>ΟΚ</sub>	output clamping current	$V_{\rm O}$ > $V_{\rm CC}$ or $V_{\rm O}$ < 0 V		-	±50	mA
Vo	output voltage	Active mode	[1][2]	-0.5	+6.5	V
		Power-down mode	[1][2]	-0.5	+6.5	V
I <sub>O</sub>	output current	$V_{O} = 0 V$ to $V_{CC}$		-	±50	mA
I <sub>CC</sub>	supply current			-	100	mA
I <sub>GND</sub>	ground current			-100	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	<u>[3]</u>	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When  $V_{CC} = 0 V$  (Power-down mode), the output voltage can be 5.5 V in normal operation.

For SC-88 and SC-74 packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K. [3] For XSON6 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

#### **Recommended operating conditions** 9.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage		1.65	-	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	Active mode	0	-	V <sub>CC</sub>	V
		Power-down mode; $V_{CC} = 0 V$	0	-	5.5	V
T <sub>amb</sub>	ambient temperature		-40	-	+125	°C

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## **10. Static characteristics**

### Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
T <sub>amb</sub> = -4	0 °C to +85 °C	·		1		I
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_0 = 100 \ \mu\text{A}; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.45	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.3	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.55	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.55	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_0 = -100 \ \mu\text{A}; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	$V_{CC}-0.1$	-	-	V
		$I_0 = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	V
		$I_0 = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_0 = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	V
		$I_0 = -24$ mA; $V_{CC} = 3.0$ V	2.3	-	-	V
		$I_0 = -32$ mA; $V_{CC} = 4.5$ V	3.8	-	-	V
lı	input leakage current	$V_1 = 5.5 \text{ V or GND}; V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	±0.1	±5	μA
I <sub>OFF</sub>	power-off leakage current	$V_{1} \text{ or } V_{O} = 5.5 \text{ V}; V_{CC} = 0 \text{ V}$	-	±0.1	±10	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	0.1	10	μA
$\Delta I_{CC}$	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V to 5.5 V}$	-	5	500	μA
Cı	input capacitance		-	2.5	-	pF
T <sub>amb</sub> = -4	0 °C to +125 °C					
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{T+}$ or $V_{T-}$				
		$I_0 = 100 \ \mu\text{A}; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.7	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.6	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.8	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.8	V
V <sub>он</sub>	HIGH-level output voltage	$V_{I} = V_{T+}$ or $V_{T-}$				
		$I_0 = -100 \ \mu A; V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	V <sub>CC</sub> – 0.1	-	-	V
		$I_0 = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V
		$I_0 = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V
		$I_0 = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V
		$I_0 = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	-	-	V
		$I_0 = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.4	-	-	V
lı	input leakage current	$V_{I} = 5.5 \text{ V or GND}; V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	±100	μA
				1		

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At recommended operating conditions; voltages are referenced to GND (ground = $0 \text{ V}$ ).							
Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit	
I <sub>OFF</sub>	power-off leakage current	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	±200	μΑ	
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	-	200	μA	
$\Delta I_{CC}$	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V} \text{ to } 5.5 \text{ V}$	-	-	5000	μA	

#### Static characteristics ... continued Table 8.

[1] Typical values are measured at maximum V<sub>CC</sub> and T<sub>amb</sub> = 25 °C.

### **11. Dynamic characteristics**

#### Table 9. **Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

Symbol	Parameter	Conditions	–40 °C to +85 °C		–40 °C to +125 °C		Unit	
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
t <sub>pd</sub>	propagation delay	A, B, C to Y; see <u>Figure 12</u> [2]						
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	1.0	6.0	14.4	1.0	18.0	ns
		$V_{CC}$ = 2.3 V to 2.7 V	0.5	3.5	8.3	0.5	10.4	ns
		$V_{CC} = 2.7 V$	0.5	4.2	8.5	0.5	10.6	ns
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	0.5	3.8	6.3	0.5	7.9	ns
		$V_{CC} = 4.5 V \text{ to } 5.5 V$	0.5	3.0	5.1	0.5	6.4	ns
C <sub>PD</sub>	power dissipation capacitance	$V_{CC} = 3.3 \text{ V}; \text{ V}_{I} = \text{GND to V}_{CC}$ [3]	-	20	-	-	-	pF

[1] Typical values are measured at nominal V<sub>CC</sub> and at  $T_{amb}$  = 25 °C.

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ 

[3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

C<sub>L</sub> = output load capacitance in pF;

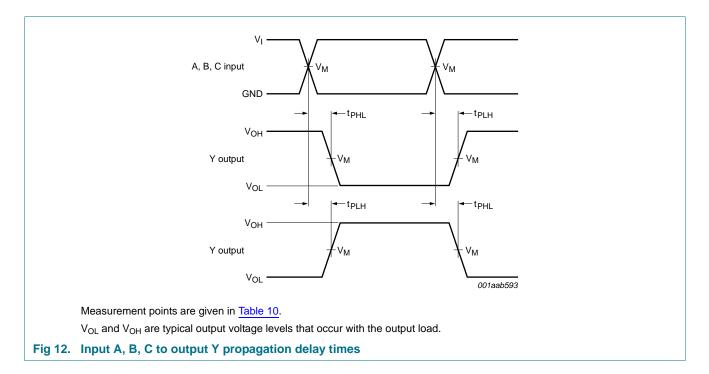
 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

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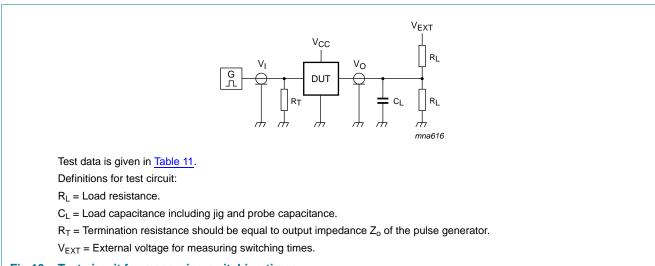
## 12. Waveforms



#### Table 10. Measurement points

Supply voltage	Input	Output	
V <sub>cc</sub>	V <sub>M</sub>	V <sub>M</sub>	
1.65 V to 1.95 V	$0.5  imes V_{CC}$	$0.5 \times V_{CC}$	
2.3 V to 2.7 V	$0.5  imes V_{CC}$	$0.5  imes V_{CC}$	
2.7 V	1.5 V	1.5 V	
3.0 V to 3.6 V	1.5 V	1.5 V	
4.5 V to 5.5 V	$0.5  imes V_{CC}$	$0.5 \times V_{CC}$	

### Low-power configurable multiple function gate



### Fig 13. Test circuit for measuring switching times

#### Table 11. Test data

Supply voltage	Input	Input		Load		
V <sub>cc</sub>	VI	$t_r = t_f$	CL	RL	t <sub>PLH</sub> , t <sub>PHL</sub>	
1.65 V to 1.95 V	V <sub>CC</sub>	≤ 2.0 ns	30 pF	1 kΩ	open	
2.3 V to 2.7 V	V <sub>CC</sub>	≤ 2.0 ns	30 pF	500 Ω	open	
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	
4.5 V to 5.5 V	V <sub>CC</sub>	$\leq$ 2.5 ns	50 pF	500 Ω	open	

### 13. Transfer characteristics

#### Table 12. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-4	–40 °C to +85 °C			–40 °C to +125 °C	
			Min	Typ[1]	Max	Min	Max	lax
V <sub>T+</sub>	positive-going threshold voltage	see Figure 14, Figure 15, Figure 16 and Figure 17						
		V <sub>CC</sub> = 1.8 V	0.70	1.02	1.20	0.67	1.20	V
		V <sub>CC</sub> = 2.3 V	1.11	1.42	1.60	1.08	1.60	V
		V <sub>CC</sub> = 3.0 V	1.50	1.79	2.00	1.47	2.00	V
		V <sub>CC</sub> = 4.5 V	2.16	2.52	2.74	2.13	2.74	V
		V <sub>CC</sub> = 5.5 V	2.61	2.99	3.33	2.58	3.33	V
V <sub>T</sub>	negative-going threshold voltage	see <u>Figure 14, Figure 15,</u> Figure 16 and <u>Figure 17</u>						
		V <sub>CC</sub> = 1.8 V	0.30	0.53	0.72	0.30	0.75	V
		V <sub>CC</sub> = 2.3 V	0.58	0.77	1.00	0.58	1.03	V
		V <sub>CC</sub> = 3.0 V	0.80	1.04	1.30	0.80	1.33	V
		V <sub>CC</sub> = 4.5 V	1.21	1.55	1.90	1.21	1.93	V
		V <sub>CC</sub> = 5.5 V	1.45	1.86	2.29	1.45	2.32	V

### Low-power configurable multiple function gate

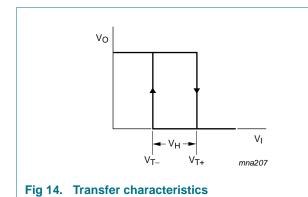
Symbol	Parameter	Conditions	-4	–40 °C to +85 °C			–40 °C to +125 °C	
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
V <sub>H</sub> hysteresis	hysteresis voltage	$(V_{T+} - V_{T-});$ see <u>Figure 14</u> , <u>Figure 15</u> , <u>Figure 16</u> and <u>Figure 17</u>						
		V <sub>CC</sub> = 1.8 V	0.30	0.48	0.62	0.23	0.62	V
		V <sub>CC</sub> = 2.3 V	0.40	0.64	0.80	0.34	0.80	V
		V <sub>CC</sub> = 3.0 V	0.50	0.75	1.00	0.44	1.00	V
		$V_{CC} = 4.5 V$	0.71	0.97	1.20	0.65	1.20	V
		V <sub>CC</sub> = 5.5 V	0.71	1.13	1.40	0.65	1.40	V

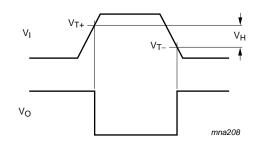
#### Table 12. Transfer characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

[1] Typical values are measured at  $T_{amb} = 25 \ ^{\circ}C$ .

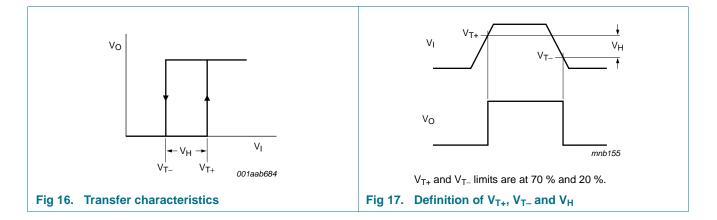
### 14. Waveforms transfer characteristics





 $V_{T+}$  and  $V_{T-}$  limits are at 70 % and 20 %.

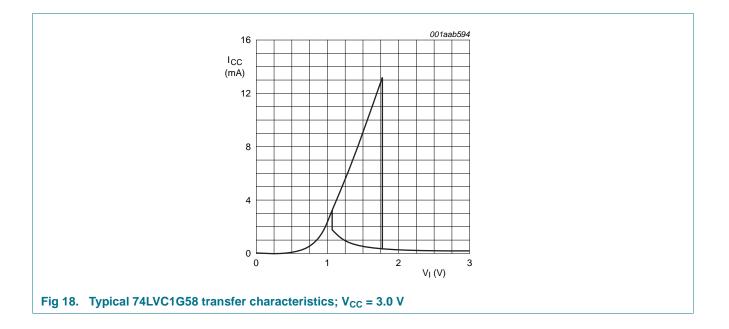




### **NXP Semiconductors**

## 74LVC1G58

### Low-power configurable multiple function gate

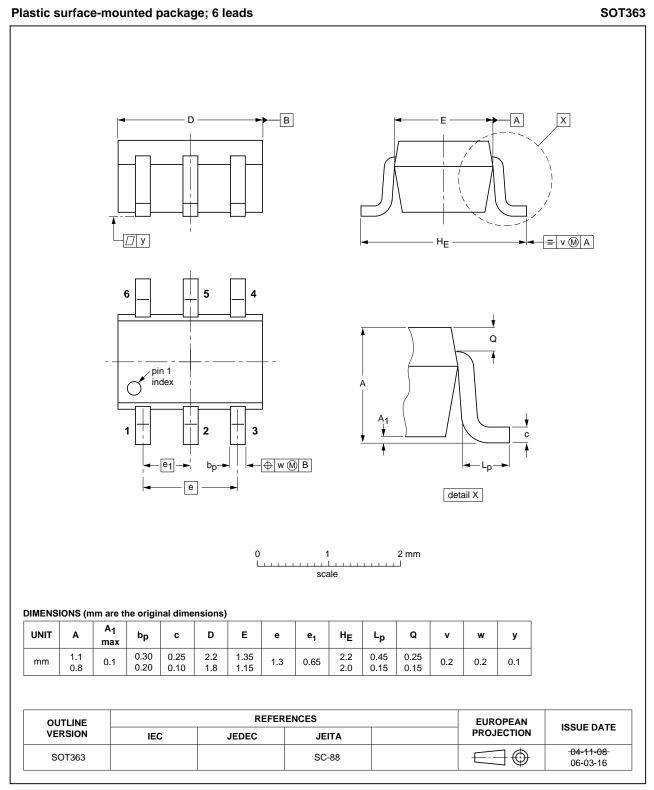


### **NXP Semiconductors**

## 74LVC1G58

Low-power configurable multiple function gate

### 15. Package outline



#### Fig 19. Package outline SOT363 (SC-88)

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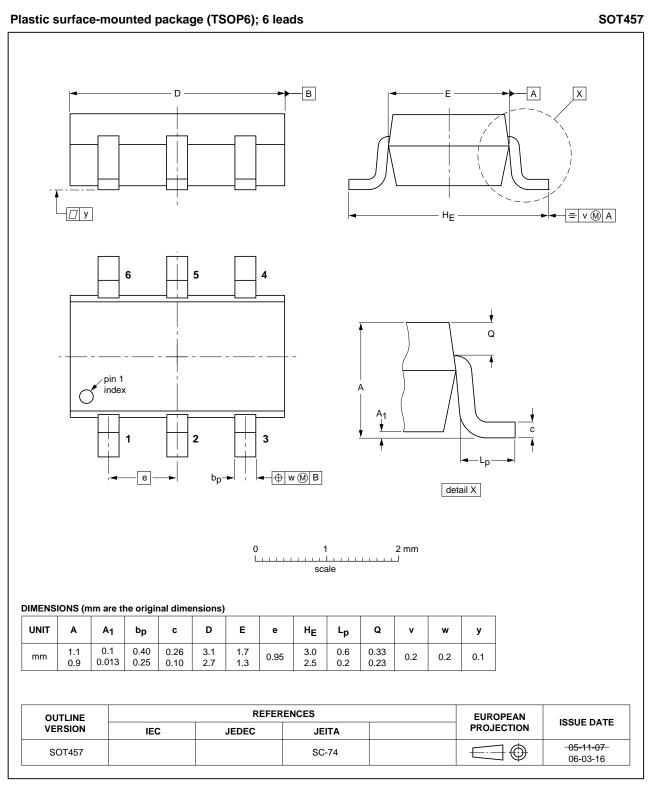


Fig 20. Package outline SOT457 (TSOP6)

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#### Low-power configurable multiple function gate

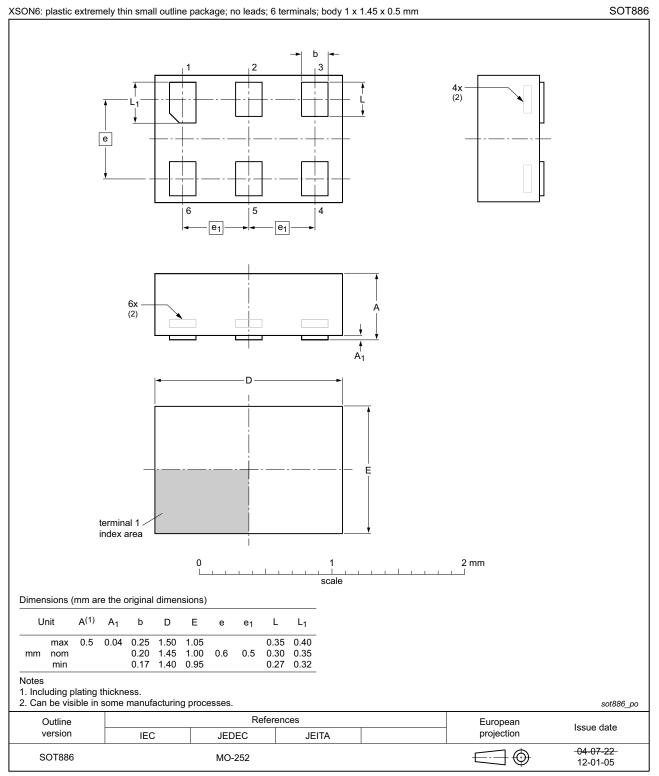


Fig 21. Package outline SOT886 (XSON6)

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#### Low-power configurable multiple function gate

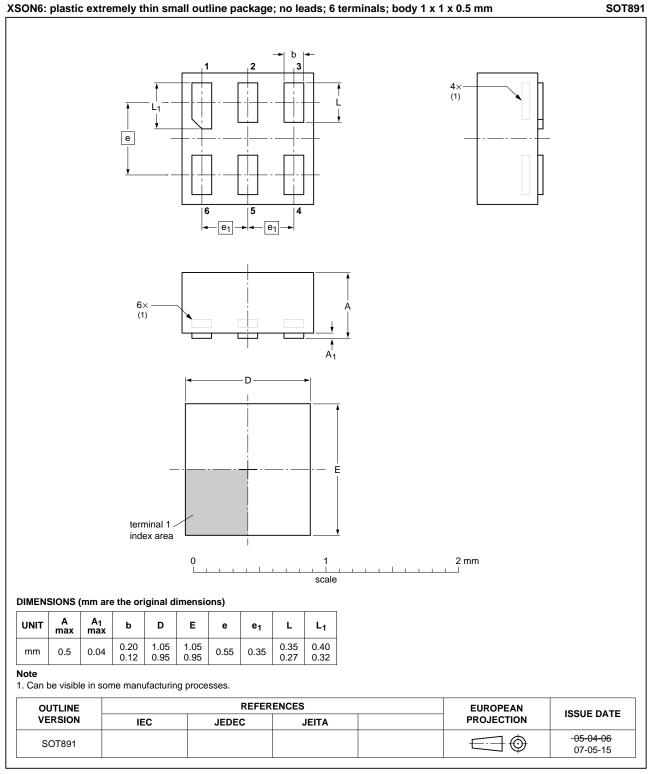
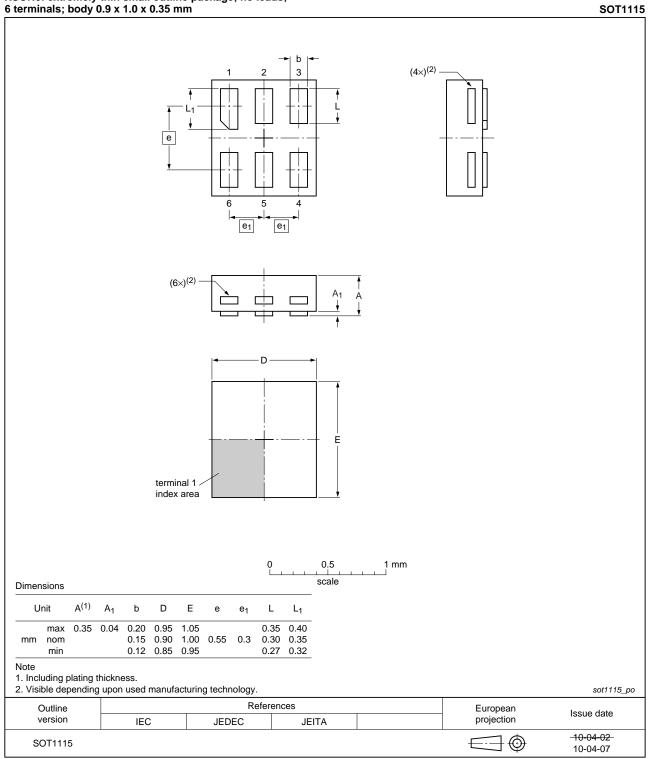


Fig 22. Package outline SOT891 (XSON6)

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Low-power configurable multiple function gate

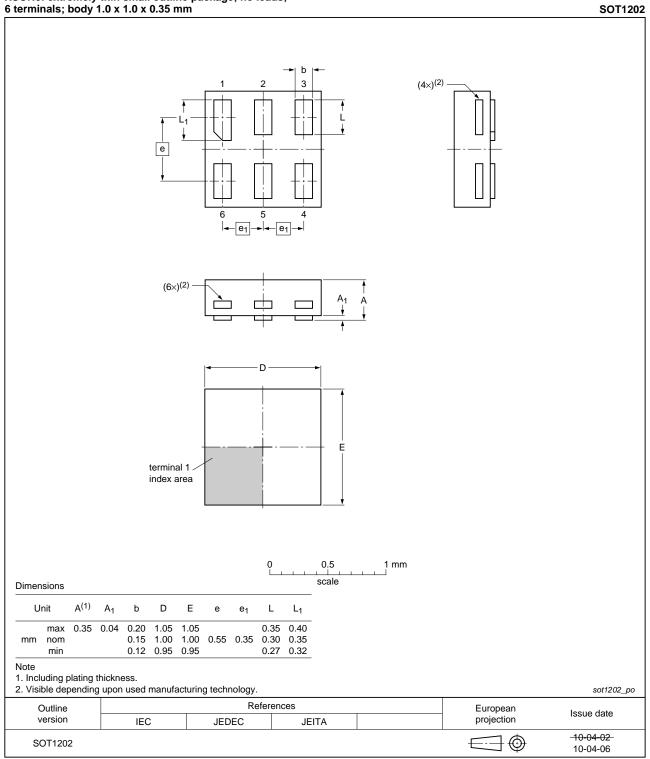


## XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 23. Package outline SOT1115 (XSON6)

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Low-power configurable multiple function gate



XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 24. Package outline SOT1202 (XSON6)

74LVC1G58 **Product data sheet** 

Low-power configurable multiple function gate

## **16. Abbreviations**

Table 13. Abbreviations			
Acronym	Description		
CMOS	Complementary Metal Oxide Semiconductor		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
HBM	Human Body Model		
MM	Machine Model		
TTL	Transistor-Transistor Logic		

## 17. Revision history

### Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G58 v.8	20140422	Product data sheet	-	74LVC1G58 v.7
Modifications:	<ul> <li>Package ou</li> </ul>	tline drawing of SOT886 (Fi	gure 21) modified.	
74LVC1G58 v.7	20111206	Product data sheet	-	74LVC1G58 v.6
Modifications:	<ul> <li>Legal pages</li> </ul>	updated.		
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74LVC1G58 v.5	20101015	Product data sheet	-	74LVC1G58 v.4
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### **18. Legal information**

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
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